

TrenchT2™ Power MOSFET

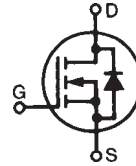
IXTA260N055T2-7

$$V_{DSS} = 55V$$

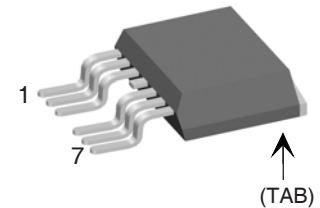
$$I_{D25} = 260A$$

$$R_{DS(on)} \leq 3.3m\Omega$$

N-Channel Enhancement Mode
Avalanche Rated



TO-263 (7-lead)



Pins: 1 - Gate
2, 3 - Source
5,6,7 - Source
TAB (8) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	55	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	55	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ C$	260	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	780	A
I_A	$T_C = 25^\circ C$	100	A
E_{AS}	$T_C = 25^\circ C$	600	mJ
P_D	$T_C = 25^\circ C$	480	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
T_{sold}	Plastic body for 10 seconds	260	$^\circ C$
Weight		3	g

Features

- International standard package
- $175^\circ C$ Operating Temperature
- High current handling capability
- Avalanche rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

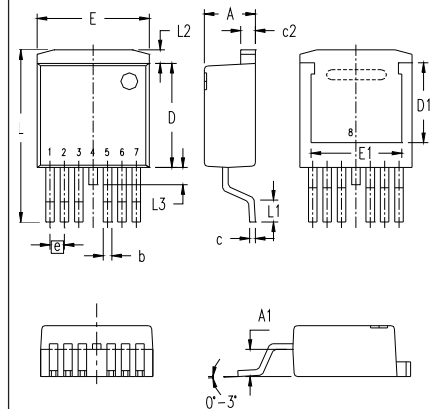
Applications

- Automotive
 - Motor Drives
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	55		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 150^\circ C$			150 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2			3.3 $m\Omega$

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1	55	94	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		10.8	nF
C_{oss}			1460	pF
C_{rss}			215	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 100\text{A}$ $R_G = 2\Omega$ (External)		20	ns
t_r			27	ns
$t_{d(off)}$			36	ns
t_f			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		140	nC
Q_{gs}			52	nC
Q_{gd}			32	nC
R_{thJC}			0.31	$^\circ\text{C/W}$

TO-263 (7-lead) (IXTA..7) Outline



- Pins: 1 - Gate
 2, 3 - Source
 4 - Drain
 5,6,7 - Source
 Tab (8) - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			260 A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			1000 A
V_{SD}	$I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 130\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 27\text{V}$		60	ns
I_{RM}			3.4	A
Q_{RM}			102	nC

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

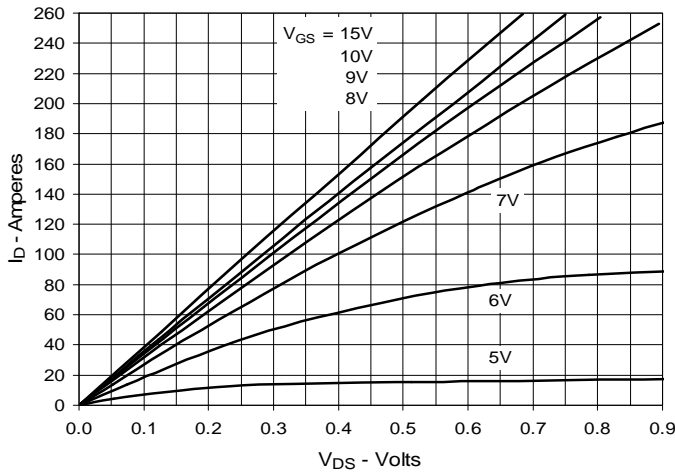


Fig. 2. Extended Output Characteristics @ 25°C

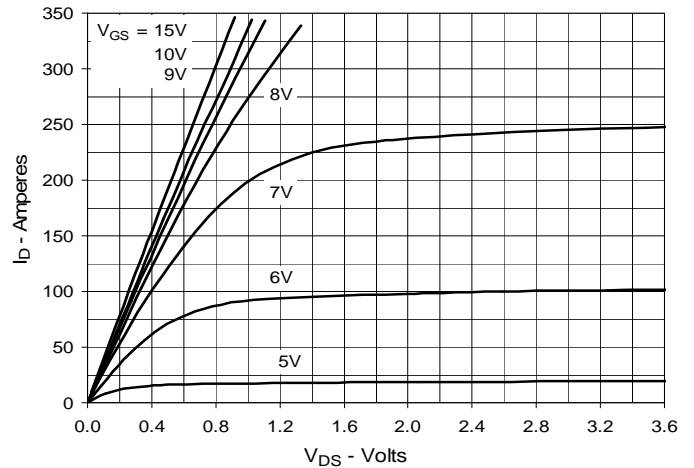


Fig. 3. Output Characteristics @ 150°C

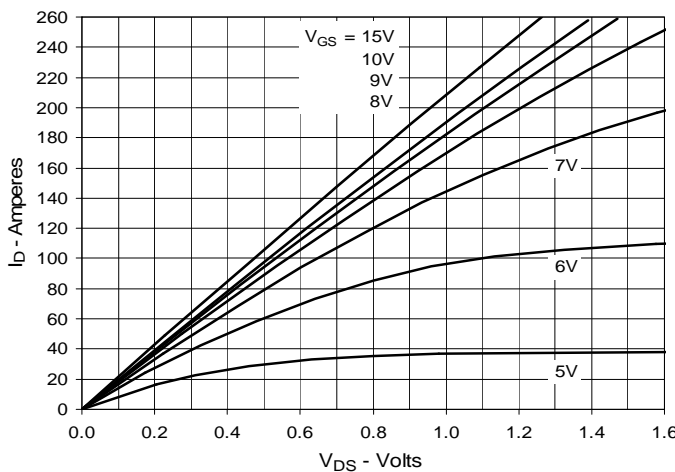


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 130A$ Value vs. Junction Temperature

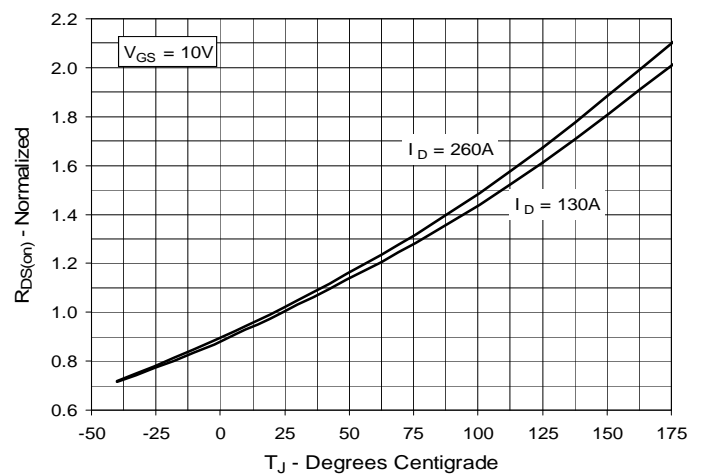


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 130A$ Value vs. Drain Current

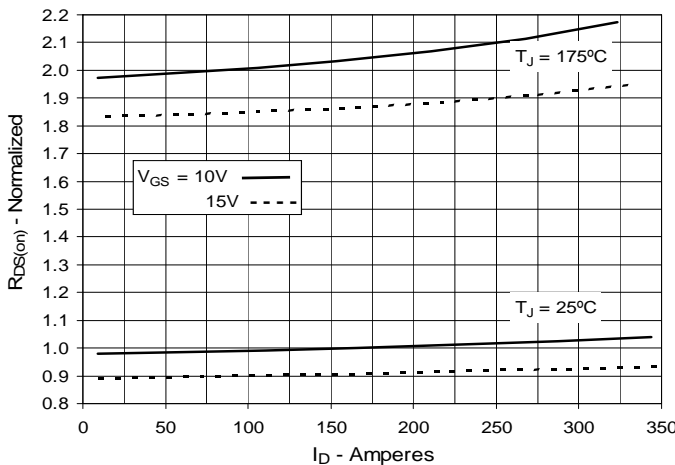


Fig. 6. Drain Current vs. Case Temperature

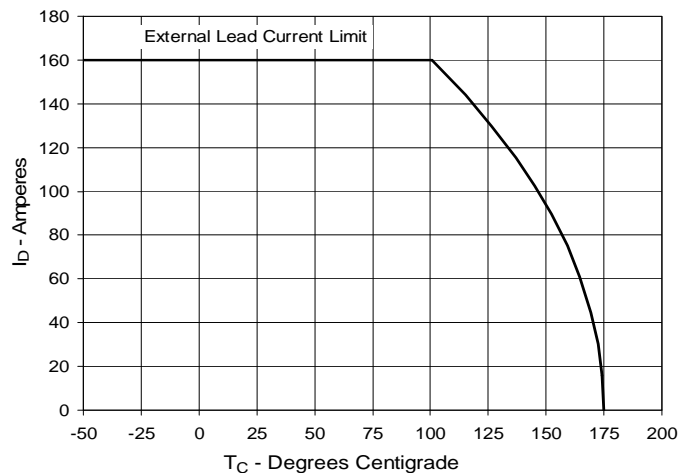


Fig. 7. Input Admittance

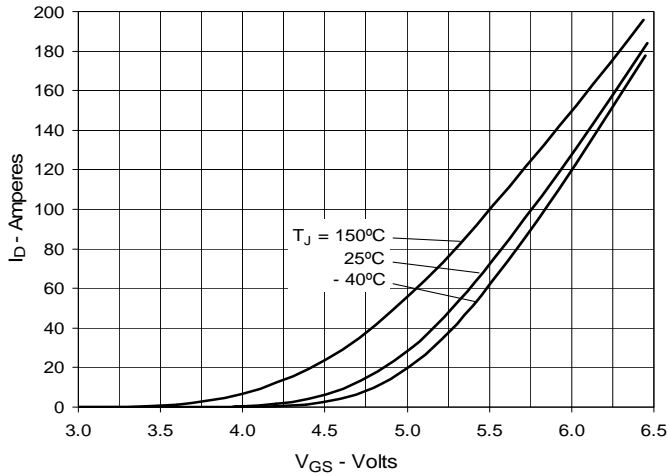


Fig. 8. Transconductance

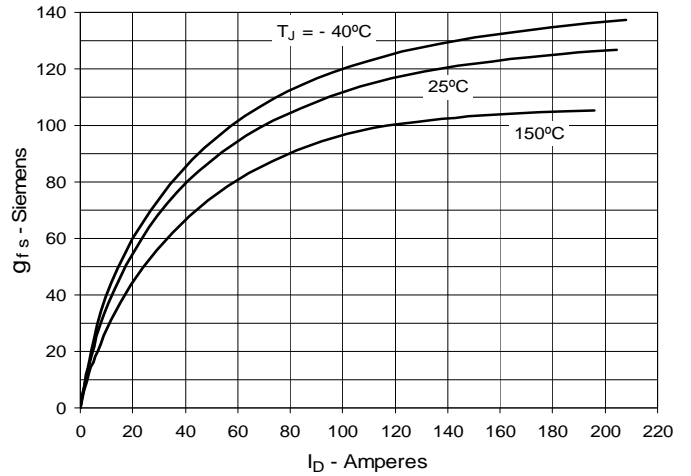


Fig. 9. Forward Voltage Drop of Intrinsic Diode

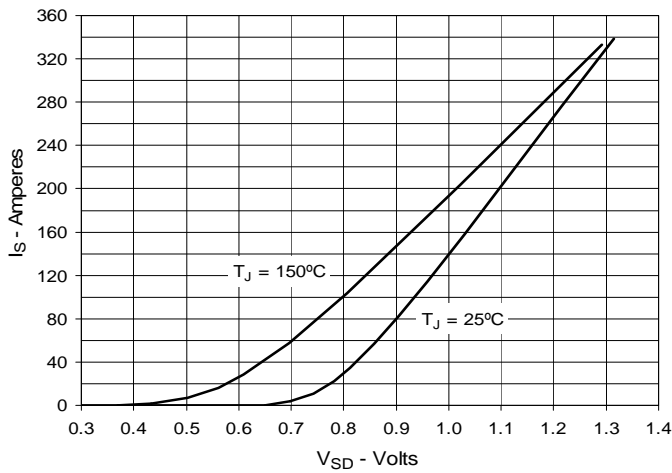


Fig. 10. Gate Charge

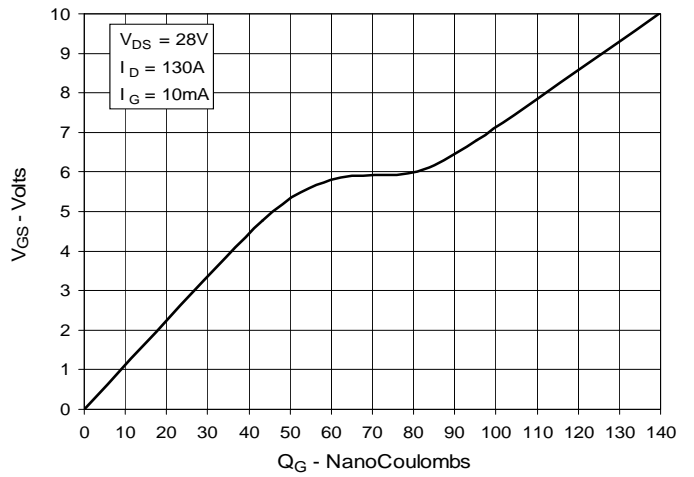


Fig. 11. Capacitance

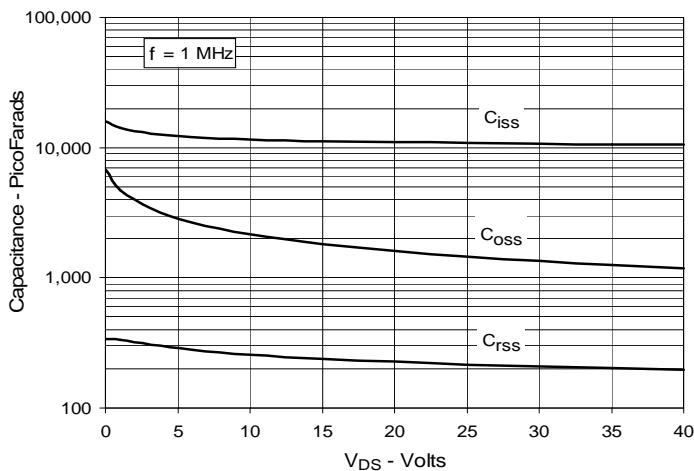
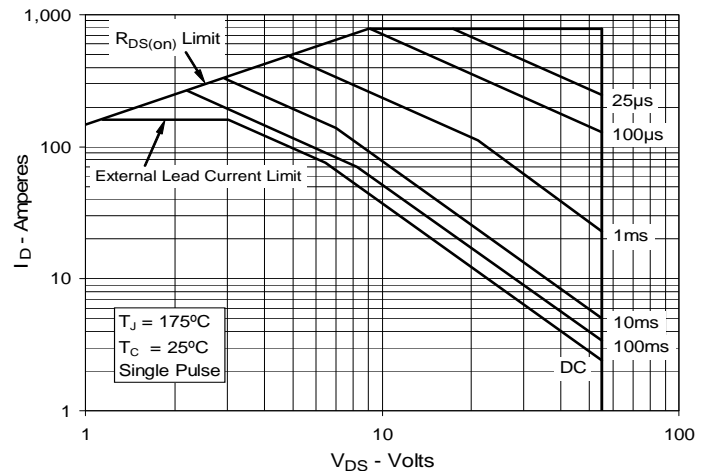


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

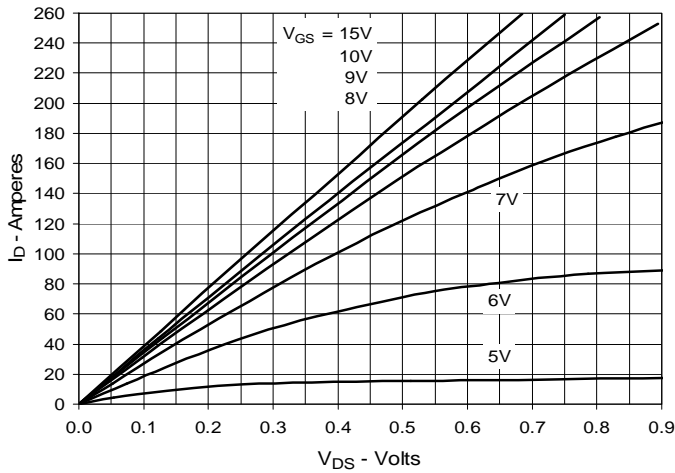
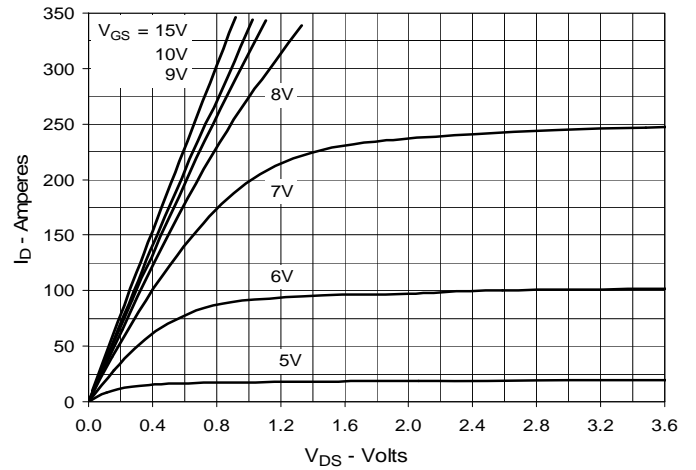
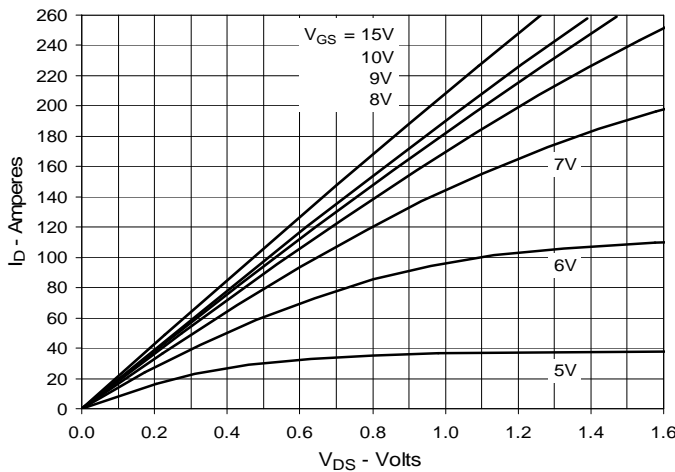
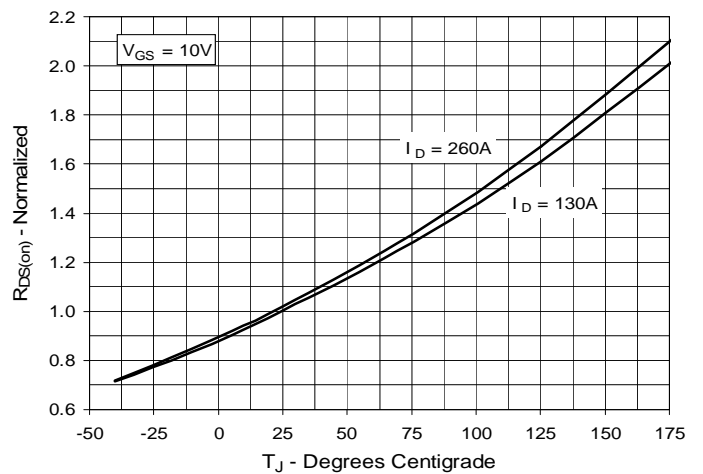
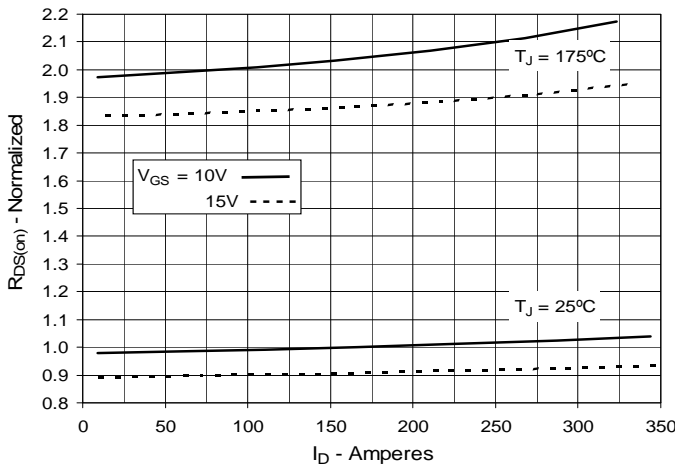
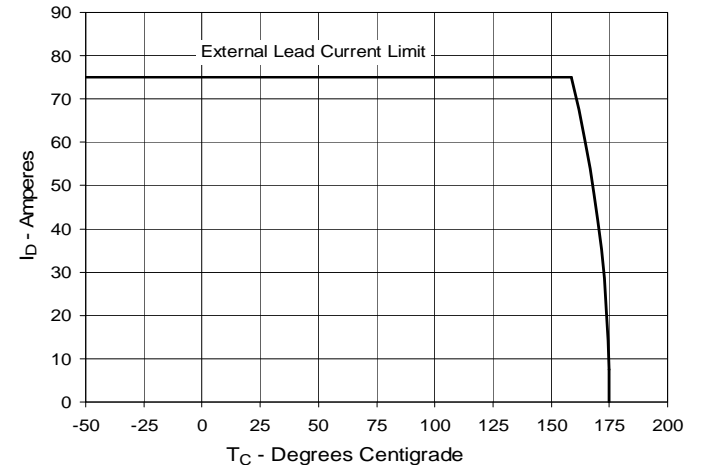
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 150°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 130\text{A}$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 130\text{A}$ Value
vs. Drain Current**

Fig. 6. Drain Current vs. Case Temperature


Fig. 19. Maximum Transient Thermal Impedance

